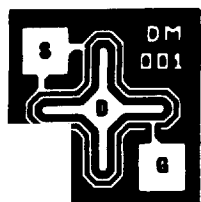


PRODUCT CATALOG

N-CHANNEL ENHANCEMENT DMOS FET

CHIP NUMBER

FMNZ35.3



.020"
(0.508mm)

.020"
(0.508mm)

Die Size: 20 x 20 (mil)
0.508 x 0.508(mm)
4 x 4 (mil)
Pad Size: 0.102 x 0.102(mm)
BODY-SUBSTRATE

CONTACT METALLIZATION

Top Contact: > 12,000
Å Aluminum

Backside Contact: 3,000 Å Gold

ASSEMBLY RECOMMENDATIONS

It is advisable that:

- the die be eutectically mounted with gold silicon preform 98/2%.
- 1 mil (0.0254mm) aluminum wire be ultrasonically attached to the top contact.

TYPICAL ELECTRICAL CHARACTERISTICS

PARAMETER	MIN.	TYP	MAX.	UNIT	TEST CONDITIONS
B_{VDS}	20	33		V	$I_D = 1.0\mu A$, $V_{GS} = 0$, $V_{BS} = 0$
I_{DSS}		0.01	10	nA	$V_{DS} = 10V$, $V_{GS} = 0$, $V_{BS} = 0$
I_{GSS}		0.01	1	nA	$V_{GS} = 10V$, $V_{BS} = V_{BD} = 0$
V_{TH}	0.1	1.0	2.5	V	$V_{DS} = V_{GS} = V_{TH}$, $I_D = 1\mu A$
g_{fs}	10	15		mmho	$V_{DS} = 10V$, $I_D = 20mA$, $f = 1KHz$
R_{DS}		50	70	Ω	$I_{DS} = 0.1mA$, $V_{GS} = 5.0V$
C_{iss}			3.6	pF	$V_{DS} = 15V$, $I_D = 20mA$, $f = 1MHz$
C_{oss}			1.3	pF	$V_{DS} = 15V$, $I_D = 20mA$, $f = 1MHz$
C_{rss}			0.35	pF	$V_{DS} = 15V$, $I_D = 20mA$, $f = 1MHz$

TYPICAL DEVICE TYPES: SDF9210, SDF9212, SDF9214, SDF8200, SDF8202

N-CHANNEL ENHANCEMENT DMOS FET

CHIP TYPE FMNZ35.3, FMN35.3

